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Silicon epitaxial wafers with buried layers

埋层硅外延片

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Foreword

This document is in accordance with the provisions of GB/T 1.1-2020 "Guidelines for standardization work Part 1: Structure and drafting rules for standardization documents" Drafting is required.

Please note that some of the contents of this document may involve patents. The issuing

organization of this document does not assume the responsibility for identifying patents.

This document was prepared by the National Technical Committee on Semiconductor Equipment and Materials Standardization (SAC/TC 203) and the National Technical Committee on Semiconductor Equipment and Materials Standardization (SAC/TC 203).

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Buried silicon epitaxial wafer

1 Scope

This document specifies the product classification, technical requirements, test methods, inspection rules and marking, packaging, transportation, storage, etc. of buried silicon epitaxial wafers.

Storage, accompanying documents and order form contents.

This document is applicable to the production, manufacturing, testing, analysis and quality evaluation of silicon epitaxial wafers with buried layer structures. The products are mainly used for the production of integrated Circuit chips and semiconductor discrete devices.

2 Normative references

GB/T 1550

GB/T 2828.1-2012

GB/T 6617

GB/T 6624

GB/T 12964

GB/T 13389

GB/T 14139

GB/T 14141

GB/T 14142

GB/T 14146

GB/T 14264

GB/T 14847

GB/T 19921

GB/T 24578

GB/T 29507

GB/T 32280

GB/T 35310.200

GB/T 39145

3 Terms and definitions

The terms and definitions defined in GB/T 14264 and the following apply to this document.

3.1

A wafer obtained by epitaxially growing a semiconductor silicon single crystal thin film layer on a buried layer.